Ordering number : ENA0745

SANYO Semiconductors

DATA SHEET

N-Channel Silicon MOSFET

2SK4101LS — General-Purpose Switching Device Applications

Features

- Low ON-resistance, low input capacitance, ultrahigh-speed switching.
- High reliability (Adoption of HVP process).
- Attachment workability is good by Mica-less package.
- Avalanche resistance guarantee.

Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V_{DSS}		650	V
Gate-to-Source Voltage	V_{GSS}		±30	V
Drain Current (DC)	I_{Dc}*1	Limited only by maximum temperature	7	A
	I_{Dpack}*2	SANYO's ideal heat dissipation condition	6.4	A
Drain Current (Pulse)	I_{DP}	PW≤10μs, duty cycle≤1%	28	A
Allowable Power Dissipation	P_D		2.0	W
		Tc=25°C (SANYO's ideal heat dissipation condition)	35	W
Channel Temperature	Tch		150	°C
Storage Temperature	Tstg		−55 to +150	°C
Avalanche Energy (Single Pulse) *3	E_{AS}		289	mJ
Avalanche Current *4	I_{AV}		7	A

*1 Shows chip capability

*2 Package limited

*3 V_{DD}=99V, L=10mH, I_{AV}=7A

*4 L≤10mH, single pulse

Marking : K4101

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SANYO Semiconductor Co., Ltd.

TOKYO OFFICE Tokyo Bldg., 1-10, 1 Chome, Ueno, Taito-ku, TOKYO, 110-8534 JAPAN

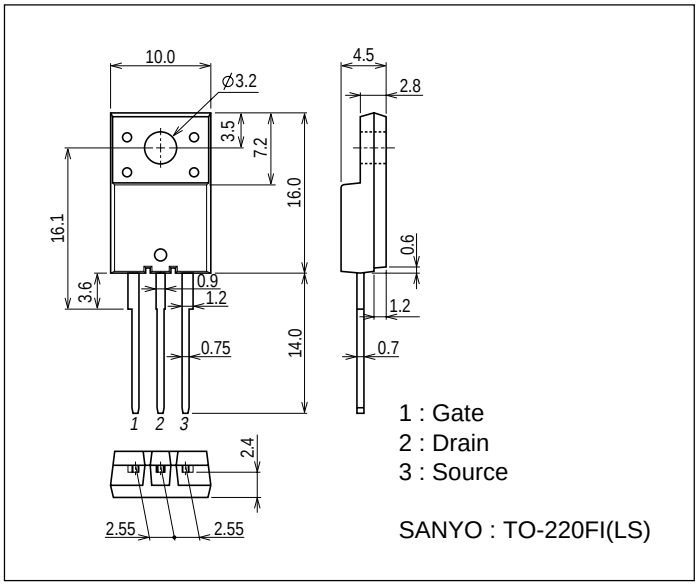
Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	I_D=10mA, V_{GS}=0V	650			V
Zero-Gate Voltage Drain Current	I_{DSS}	V_{DS}=520V, V_{GS}=0V			100	μA
Gate-to-Source Leakage Current	I_{GSS}	V_{GS}=±30V, V_{DS}=0V			±100	nA
Cutoff Voltage	V_{GS}(off)	V_{DS}=10V, I_D=1mA	3		5	V
Forward Transfer Admittance	|yfs|	V_{DS}=10V, I_D=3.5A	2.3	4.6		S
Static Drain-to-Source On-State Resistance	R_{DS}(on)	I_D=3.5A, V_{GS}=10V		0.85	1.1	Ω
Input Capacitance	Ciss	V_{DS}=30V, f=1MHz		750		pF
Output Capacitance	Coss	V_{DS}=30V, f=1MHz		136		pF
Reverse Transfer Capacitance	Crss	V_{DS}=30V, f=1MHz		28		pF
Turn-ON Delay Time	t_d(on)	See specified Test Circuit.		21		ns
Rise Time	t_r	See specified Test Circuit.		40		ns
Turn-OFF Delay Time	t_d(off)	See specified Test Circuit.		89		ns
Fall Time	t_f	See specified Test Circuit.		31		ns
Total Gate Charge	Qg	V_{DS}=200V, V_{GS}=10V, I_D=7A		28.5		nC
Gate-to-Source Charge	Qgs	V_{DS}=200V, V_{GS}=10V, I_D=7A		5.2		nC
Gate-to-Drain “Miller” Charge	Qgd	V_{DS}=200V, V_{GS}=10V, I_D=7A		16		nC
Diode Forward Voltage	V_{SD}	I_S=7A, V_{GS}=0V		0.9	1.2	V

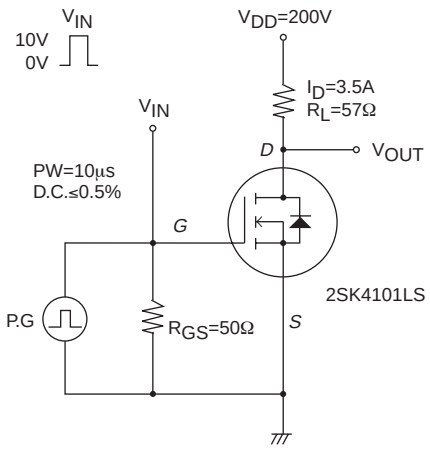
Package Dimensions

unit : mm (typ)

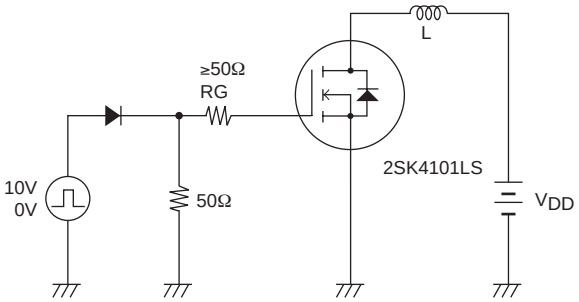
7509-002

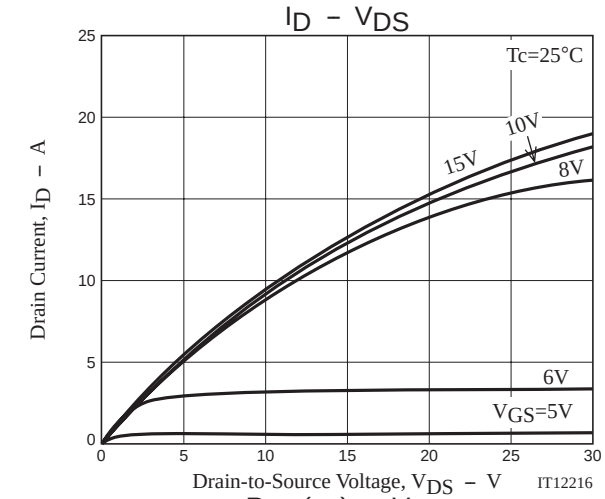


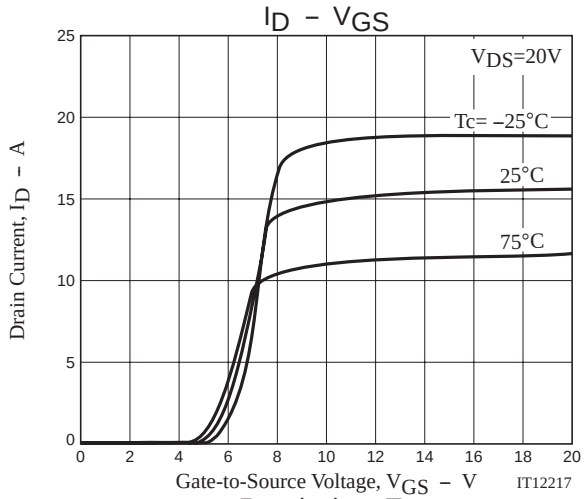
Switching Time Test Circuit

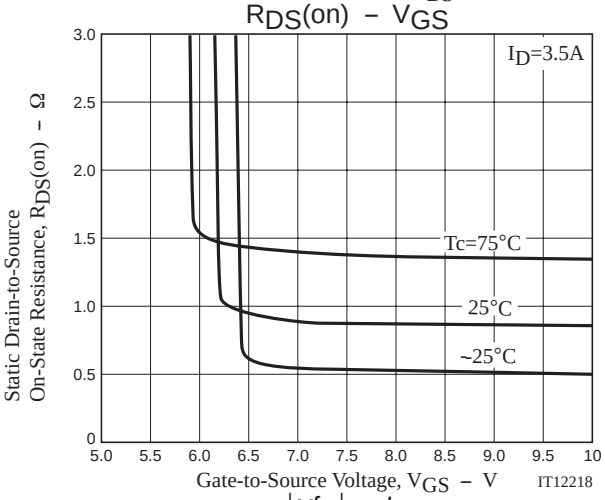


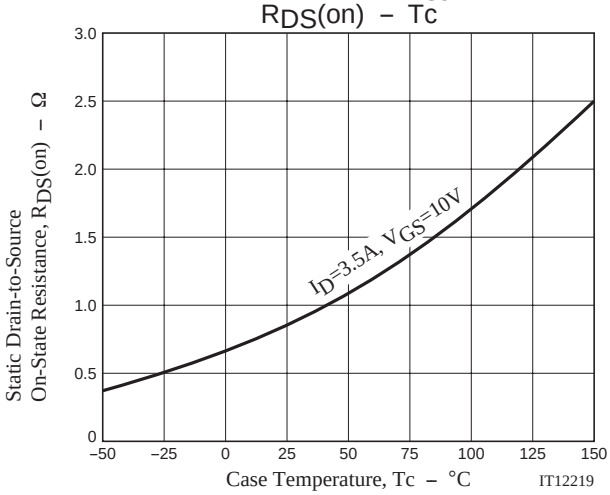
Avalanche Resistance Test Circuit

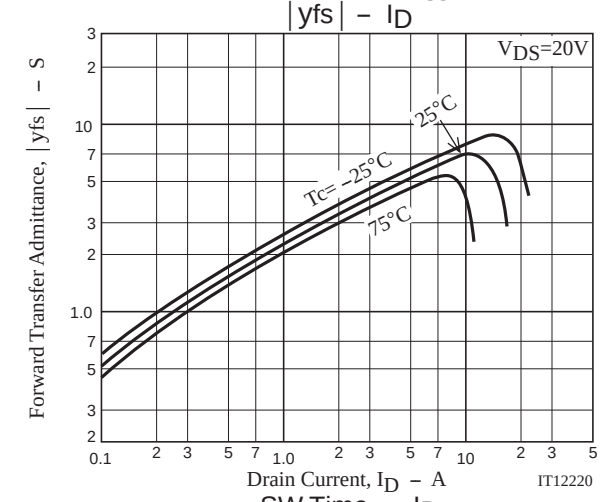


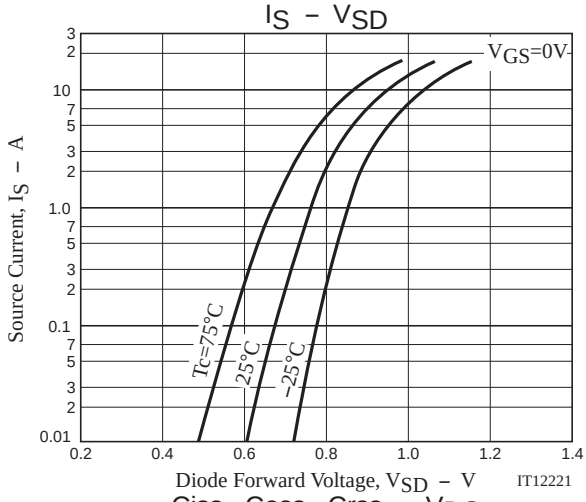

ID – VDS
Tc=25°C
10V
15V
8V
6V
VGS=5V
Drain Current, ID – A
Drain-to-Source Voltage, VDS – V
IT12216

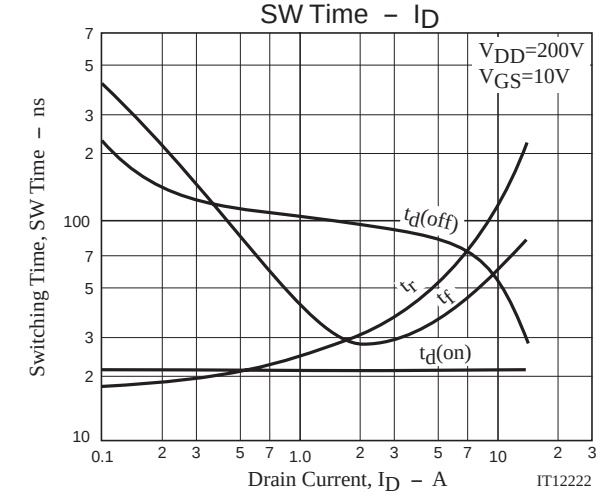

ID – VGS
VDS=20V
Tc= –25°C
25°C
75°C
Drain Current, ID – A
Gate-to-Source Voltage, VGS – V
IT12217

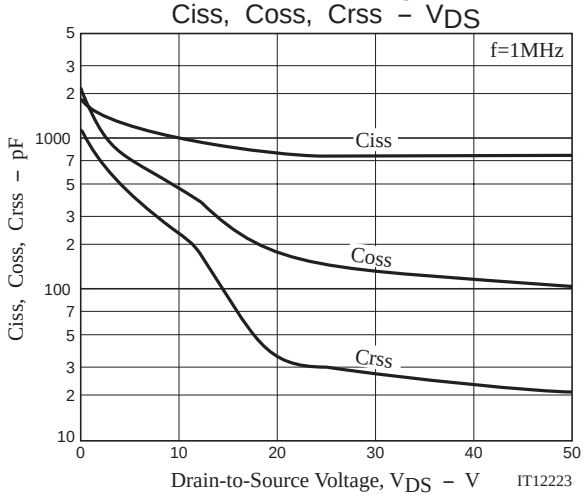

RDS(on) – VGS
ID=3.5A
Tc=75°C
25°C
–25°C
Static Drain-to-Source On-State Resistance, RDS(on) – Ω
Gate-to-Source Voltage, VGS – V
IT12218

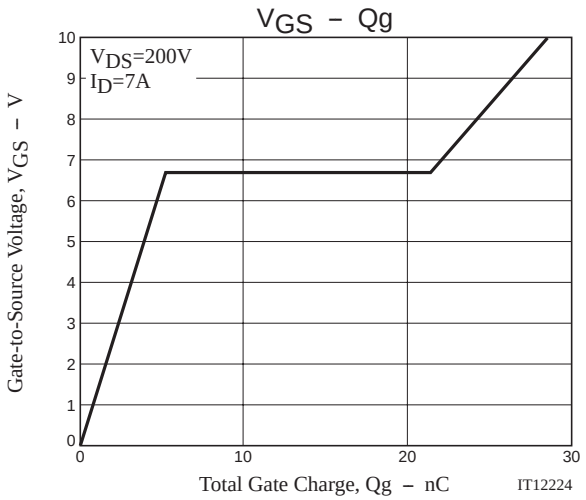

RDS(on) – Tc
ID=3.5A, VGS=10V
Static Drain-to-Source On-State Resistance, RDS(on) – Ω
Case Temperature, Tc – °C
IT12219

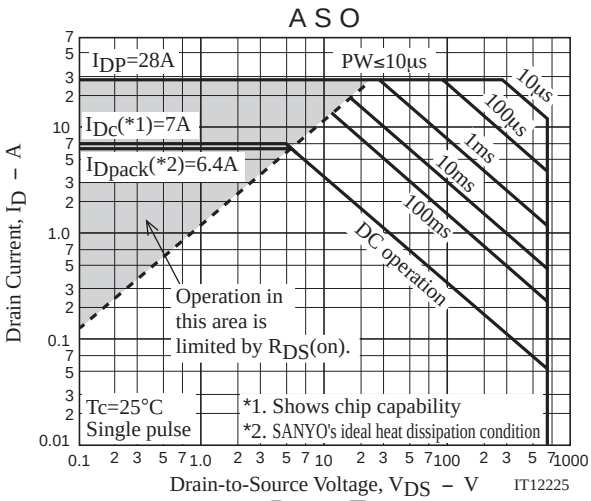

|yfs| – ID
VDS=20V
25°C
Tc= –25°C
75°C
Forward Transfer Admittance, |yfs| – S
Drain Current, ID – A
IT12220

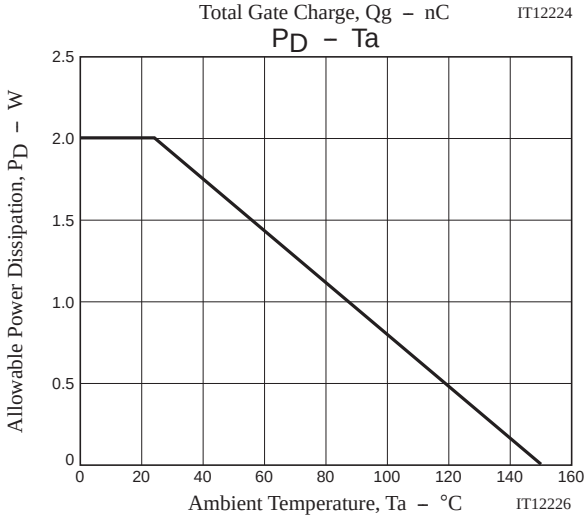

IS – VSD
VGS=0V
Tc=75°C
25°C
–25°C
Source Current, IS – A
Diode Forward Voltage, VSD – V
IT12221

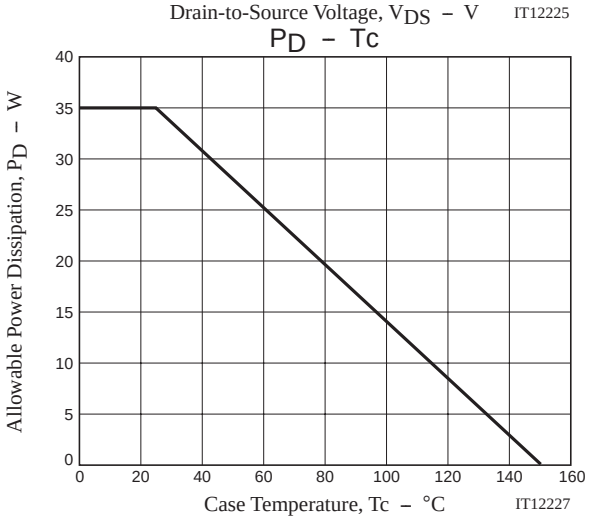

SW Time – ID
VDD=200V
VGS=10V
td(off)
tf
tr
td(on)
Switching Time, SW Time – ns
Drain Current, ID – A
IT12222

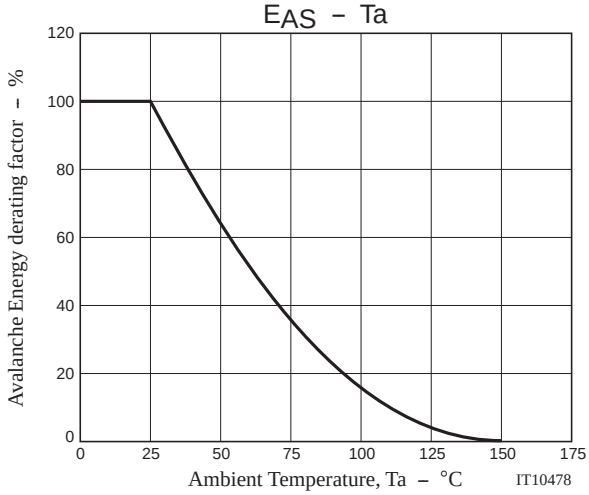

Ciss, Coss, Crss – VDS
f=1MHz
Ciss
Coss
Crss
Ciss, Coss, Crss – pF
Drain-to-Source Voltage, VDS – V
IT12223


VGS – Qg
VDS=200V
ID=7A
Gate-to-Source Voltage, VGS – V
Total Gate Charge, Qg – nC
IT12224


A S O
IDP=28A
PW≤10μs
IDC(*1)=7A
IDpack(*2)=6.4A
10μs
100μs
1ms
10ms
100ms
DC operation
Operation in this area is limited by RDS(on).
Tc=25°C
Single pulse
*1. Shows chip capability
*2. SANYO's ideal heat dissipation condition
Drain Current, ID – A
Drain-to-Source Voltage, VDS – V
IT12225


PD – Ta
Allowable Power Dissipation, PD – W
Ambient Temperature, Ta – °C
IT12226


PD – Tc
Allowable Power Dissipation, PD – W
Case Temperature, Tc – °C
IT12227


EAS – Ta
Avalanche Energy derating factor – %
Ambient Temperature, Ta – °C
IT10478

Note on usage : Since the 2SK4101LS is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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